



N-Channel 60 V (D-S), 175 °C MOSFET, Logic Level

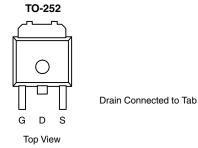
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	
60	0.0093 at V _{GS} = 10 V	50	
60	0.0122 at V _{GS} = 4.5 V	50	

FEATURES

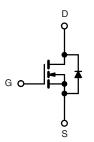
- 175 °C Junction Temperature
- TrenchFET® Power MOSFET

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





Ordering Information: SUD50N06-09L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current /T 175 °C\D	T _C = 25 °C	I_	50	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	l _D	50 ^a	
Pulsed Drain Current		I _{DM}	100	A
Continuous Source Current (Diode Conduction)		I _S	50 ^a	
Avalanche Current		I _{AS}	50	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ
Maximum Power Dissination	T _C = 25 °C	P _D	136	w
Maximum Power Dissipation	T _A = 25 °C	T D	3 ^b , 8.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 sec	D	15	18	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	40	50	°C/W
Maximum Junction-to-Case	·	R _{thJC}	0.85	1.1	

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s}$.

SUD50N06-09L

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static	•		•	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 60 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α
		V _{GS} = 10 V, I _D = 20 A		0.0074	0.0093	
5 . 6 . 6 5 h	В	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0160	Ω
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0200	
		V _{GS} = 4.5 V, I _D = 15 A			0.0122	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S
Dynamic	•		•	•		
Input Capacitance	C _{iss}			2650		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470		pF
Reverse Transfer Capacitance	C _{rss}			225		
Total Gate Charge ^c	Q_g			47	70	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC
Gate-Drain Charge ^c	Q_{gd}			12		
Turn-On Delay Time ^c	t _{d(on)}			10	20	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, R}_{L} = 0.6 \Omega$		15	25	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50	ns
Fall Time ^c	t _f	\neg		20	30	
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)			<u> </u>	
Pulsed Current	I _{SM}				100	Α
Diode Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns

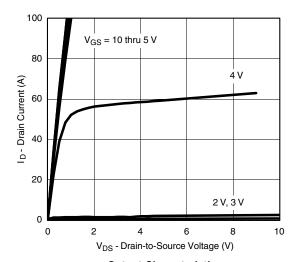
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

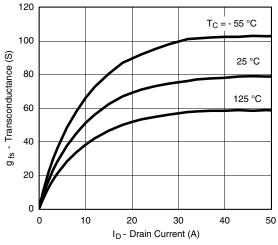
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



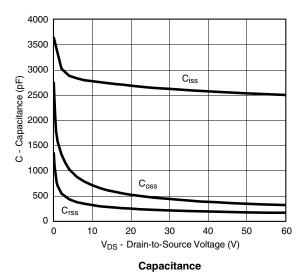
TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics

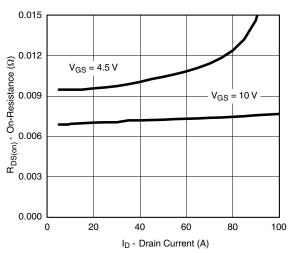


Transconductance

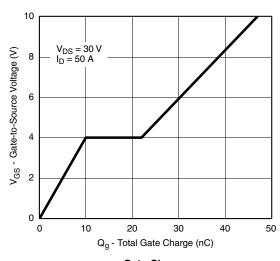


100 80 I_D - Drain Current (A) 60 40 T_C = 125 °C 20 25 55 °C 0 0 2 3 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



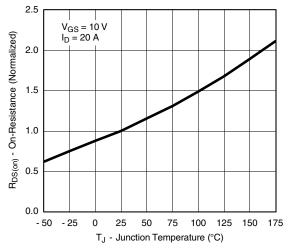
On-Resistance vs. Drain Current



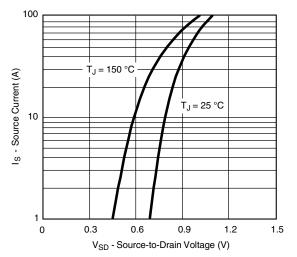
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TYPICAL CHARACTERISTICS (25 °C unless noted)



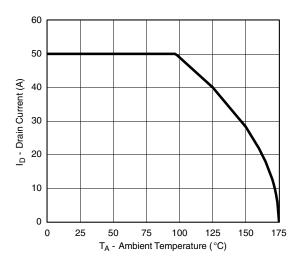
On-Resistance vs. Junction Temperature

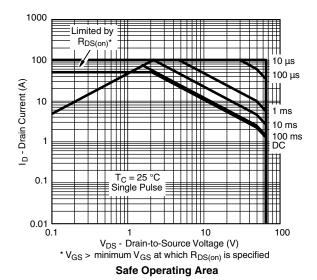


Source-Drain Diode Forward Voltage

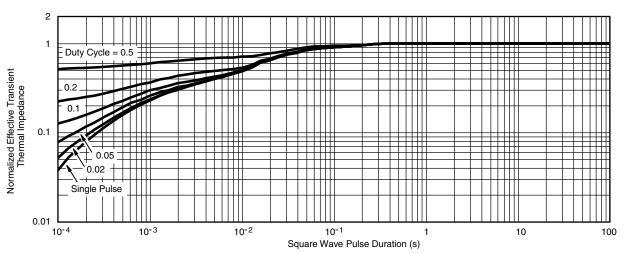


THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



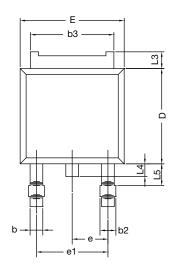
Normalized Thermal Transient Impedance, Junction-to-Case

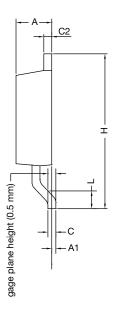
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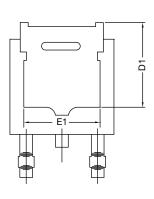


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







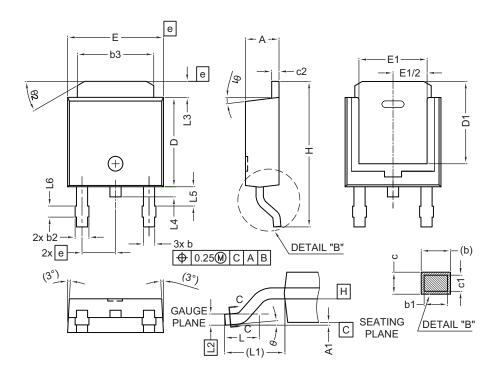
	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
Е	6.35	6.73	
E1	4.32	=	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	- 1.02		
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
Е	6.35	6.73	
E1	4.32	-	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

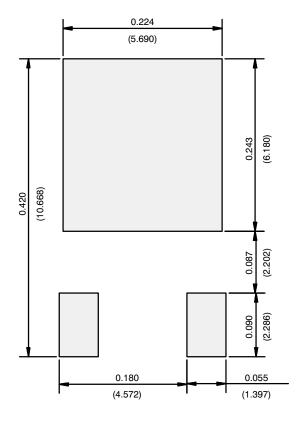
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- · Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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